

HD151TS307ARP

Spread Spectrum Clock for EMI Solution

REJ03D0022-0400Z

Rev.4.00

Jul. 08, 2004

Description

The HD151TS307ARP is a high-performance Spread Spectrum Clock modulator. It is suitable for low EMI solution.

Features

- Supports 10 MHz to 60 MHz operation. (Designed for XIN = 24 MHz and 48 MHz)
- 1 copy of clock out with spread spectrum modulation @3.3 V
- Programmable spread spectrum modulation ($\pm 0.25\%$, $\pm 0.5\%$, $\pm 1.5\%$ central spread modulation and spread spectrum disable mode.)
- SOP-8pin

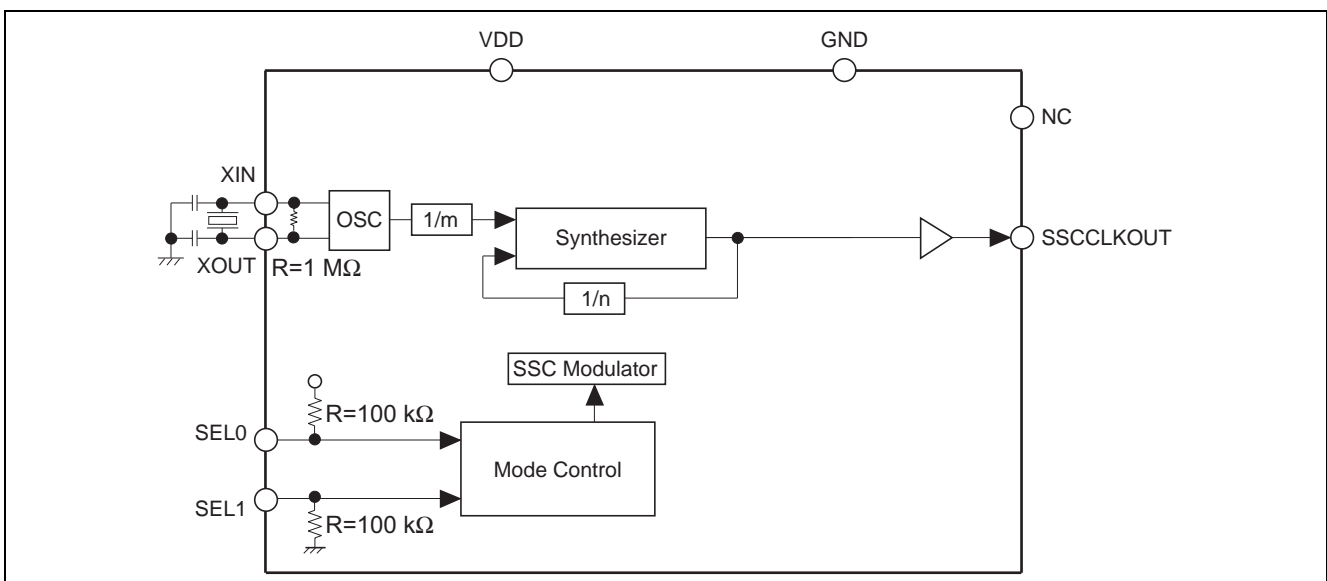
Key Specifications

- Supply voltages : VDD = 3.3 V ± 0.165 V
- Ta = 0 to 70°C operating range
- Clock output duty cycle = 50 $\pm 5\%$
- Cycle to cycle jitter = ± 250 ps typ.
- Ordering Information

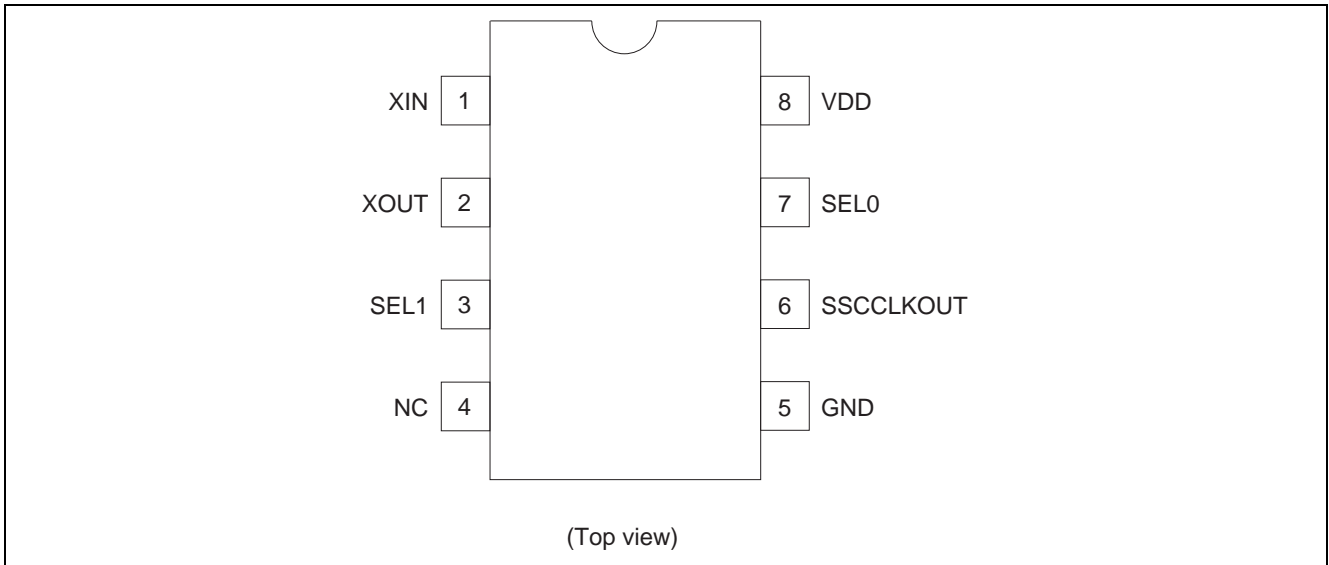
Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD151TS307ARPEL	SOP-8 pin (JEDEC)	FP-8DC	RP	EL (2,500 pcs / Reel)

Note: Please consult the sales office for the above package availability.

Block Diagram



Pin Arrangement



SSC Function Table

SEL1 :0	Spread Percentage
0 0	±0.5%
0 1	±1.5%
1 0	SSC OFF
1 1	±0.25%

Note: ±1.5% SSC is selected for default by internal pull-up & down resistors.

Clock Frequency Table

XIN(MHz)	SSCCLKOUT(MHz)
48	48 ^{*1}
24	24 ^{*1}

Notes: 1. With spread spectrum modulation.

Pin Descriptions

Pin name	No.	Type	Description
GND	5	Ground	GND pin
VDD	8	Power	Power supplies pin. Normally 3.3 V.
NC	4	NC	Don't connect any signal or VDD or GND. This pin is used for Renesas Test.
SSCCLKOUT	6	Output	Spread spectrum modulated clock output.
XIN	1	Input	Oscillator input.
XOUT	2	Output	Oscillator output.
SEL0	7	Input	SSC mode select pin. LVCMOS level input. Pull-up by internal resistor (100 kΩ).
SEL1	3	Input	SSC mode select pin. LVCMOS level input. Pull-down by internal resistor (100 kΩ).

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	VDD	-0.5 to 4.6	V	
Input voltage	V _I	-0.5 to 4.6	V	
Output voltage ^{*1}	V _O	-0.5 to VDD+0.5	V	
Input clamp current	I _{IK}	-50	mA	V _I < 0
Output clamp current	I _{OK}	-50	mA	V _O < 0
Continuous output current	I _O	±50	mA	V _O = 0 to VDD
Maximum power dissipation at Ta = 55°C (in still air)		0.7	W	
Storage temperature	T _{stg}	-65 to +150	°C	

Notes: Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

Recommended Operating Conditions

Item	Symbol	Min	Typ	Max	Unit	Conditions
Supply voltage	VDD	3.135	3.3	3.465	V	
DC input signal voltage		-0.3	—	VDD+0.3	V	
High level input voltage	V _{IH}	2.0	—	VDD+0.3	V	
Low level input voltage	V _{IL}	-0.3	—	0.8	V	
Operating temperature	T _a	0	—	70	°C	
Input clock duty cycle		45	50	55	%	

DC Electrical Characteristics

Ta = 0 to 70°C, VDD = 3.3 V±5%

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input low voltage	V _{IL}	—	—	0.8	V	
Input high voltage	V _{IH}	2.0	—	—	V	
Input current	I _I	—	—	±10	μA	V _I = 0 V or 3.465 V, VDD = 3.465 V, XIN pin
		—	—	±100		V _I = 0 V or 3.465 V, VDD = 3.465 V, SEL0, SEL1 pins
Input slew rate		1	—	4	V / ns	20% – 80%
Input capacitance	C _I	—	—	4	pF	SEL0, SEL1
Operating current		—	7	—	mA	XIN = 24 MHz, C _L = 0 pF, VDD = 3.3 V

DC Electrical Characteristics / SSC Clock Output

Ta = 0 to 70°C, VDD = 3.3 V±5%

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Output voltage	V _{OH}	3.1	—	—	V	I _{OH} = -1 mA, VDD = 3.3 V
	V _{OL}	—	—	50	mV	I _{OL} = 1 mA, VDD = 3.3 V
Output current *1	I _{OH}	—	-30	—	mA	V _{OH} = 1.5 V
	I _{OL}	—	30	—		V _{OL} = 1.5 V

Note: 1. Parameters are target of design. Not 100% tested in production.

AC Electrical Characteristics / SSC Clock Output

Ta = 25°C, VDD = 3.3 V, C_L = 15 pF

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	Notes
Cycle to cycle jitter *1,2	t _{CCS}	—	250	300	ps	SSCCLKOUT, 24 MHz	SSCOFF
		—	250	300		SSCCLKOUT, 48 MHz	SEL1:0 = 10 Fig1
		—	250	300		SSCCLKOUT, 24 MHz	SSC=±0.25%
		—	250	300		SSCCLKOUT, 48 MHz	SEL1:0 = 11 Fig1
		—	250	300		SSCCLKOUT, 24 MHz	SSC= ±1.5%
		—	250	300		SSCCLKOUT, 48 MHz	SEL1:0 = 01 Fig1
Output frequency *1,2		23.8	—	24.2	MHz	SSCCLKOUT, XIN = 24 MHz	SSCOFF SEL1:0 = 10
		47.3	—	48.7		SSCCLKOUT, XIN = 48 MHz	
		23.7	—	24.3		SSCCLKOUT, XIN = 24 MHz	SSC= ±0.25% SEL1:0 = 11
		47.2	—	48.8		SSCCLKOUT, XIN = 48 MHz	
		23.4	—	24.6		SSCCLKOUT, XIN = 24 MHz	SSC= ±1.5% SEL1:0 = 01
		46.6	—	49.4		SSCCLKOUT, XIN = 48 MHz	
Slew rate *1	t _{SL}	0.8	—	—	V/ns	@48 MHz	0.4 V to 2.4 V
Clock duty cycle *1		45	50	55	%		
Output impedance *1		—	40	—	Ω		
Spread spectrum modulation frequency *1		—	33	—	KHz	@48 MHz, SSCCLKOUT	
Input clock frequency		10	—	60	MHz		
Stabilization time *1,3		—	—	2	ms		

Notes: 1. Parameters are target of design. Not 100% tested in production.

2. Cycle to cycle jitter and output frequency are included spread spectrum modulation.

3. Stabilization time is the time required for the integrated circuit to obtain phase lock of its input signal after power up.

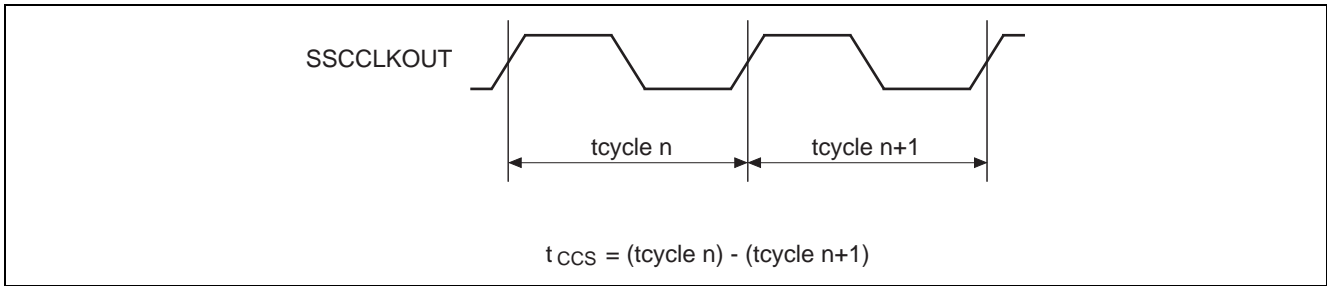


Figure 1 Cycle to cycle jitter

Application Information

1. Recommended Circuit Configuration

The power supply circuit of the optimal performance on the application of a system should refer to Fig. 2.

VDD decoupling is important to both reduce Jitter and EMI radiation.

The C1 decoupling capacitor should be placed as close to the VDD pin as possible, otherwise the increased trace inductance will negate its decoupling capability.

The C2 decoupling capacitor shown should be a tantalum type.

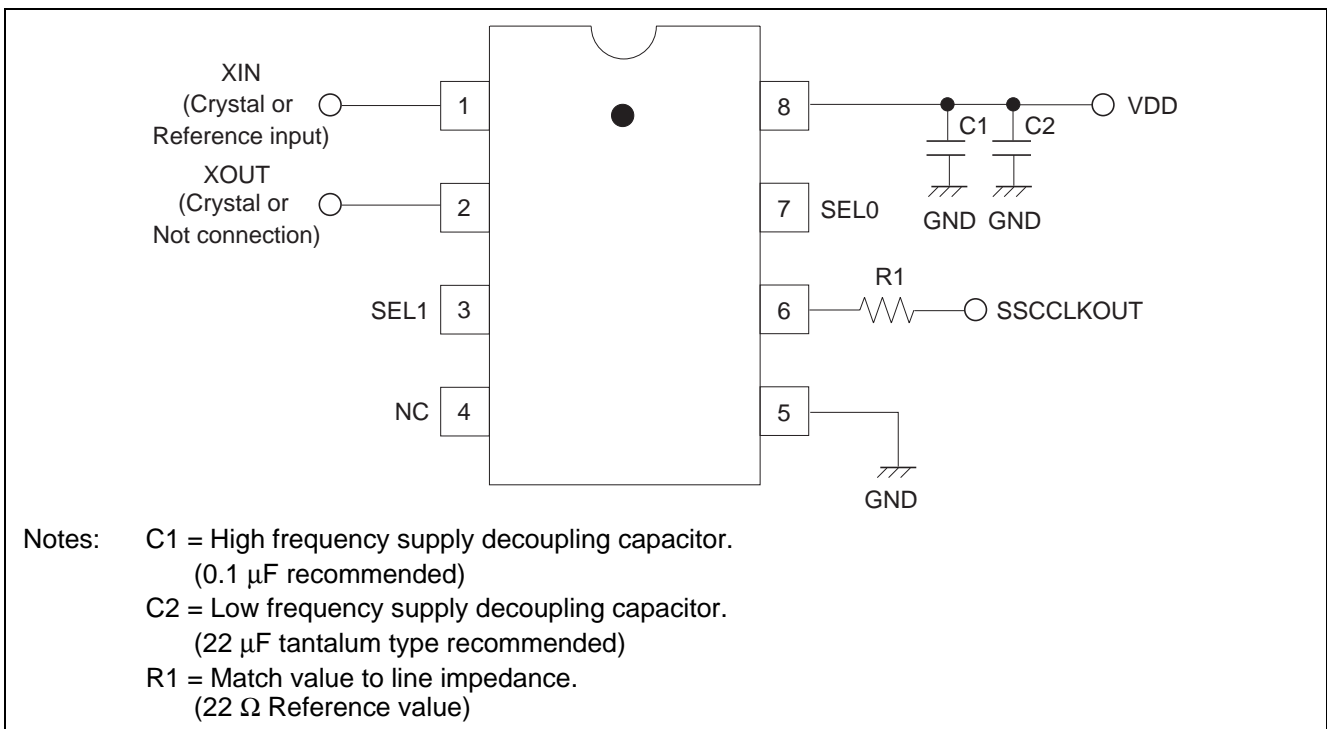


Figure 2 Recommended circuit configuration

2. Example Board Layout Configuration

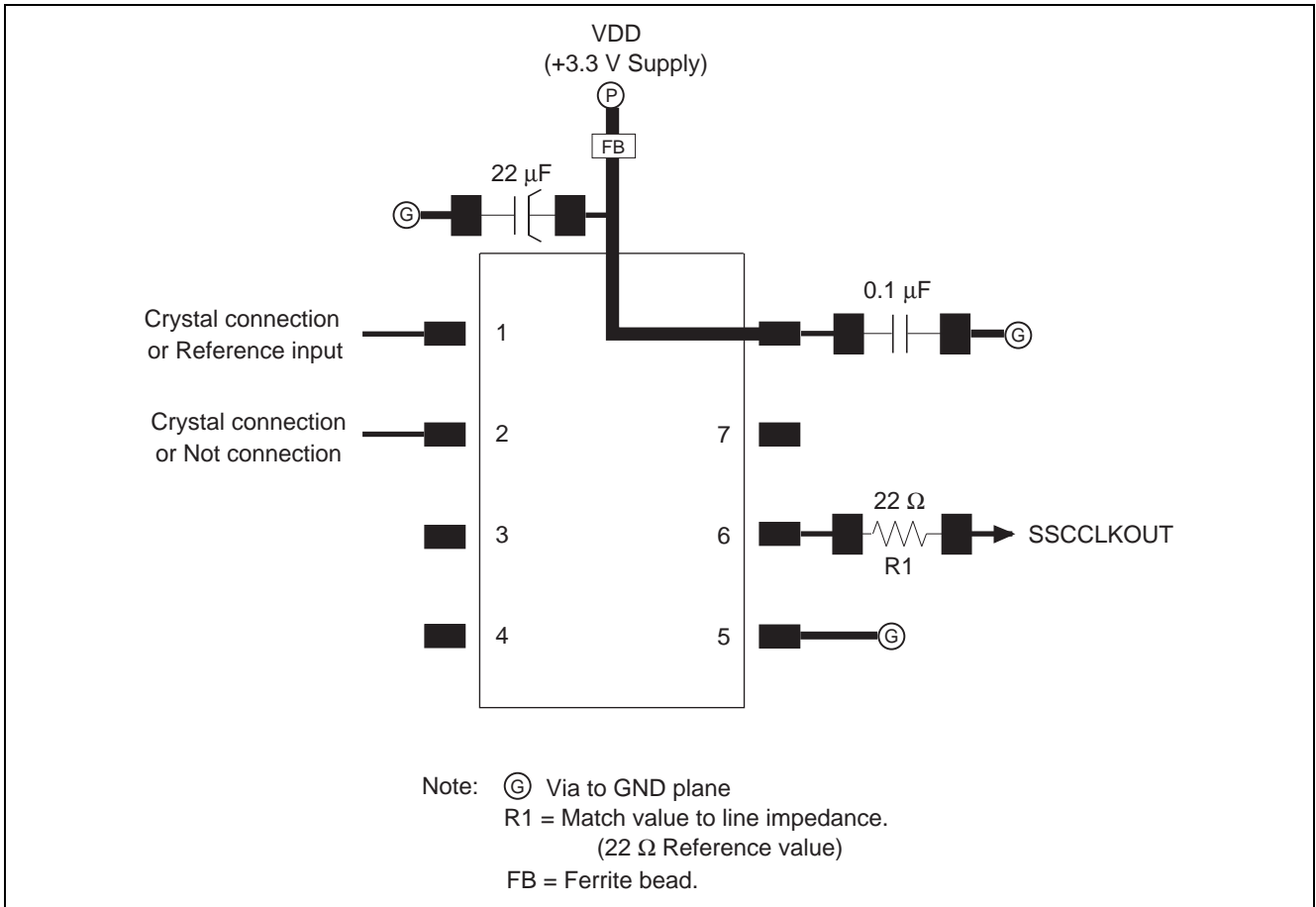


Figure 3 Example Board Layout

3. Example of TS300 EMI Solution IC's Application

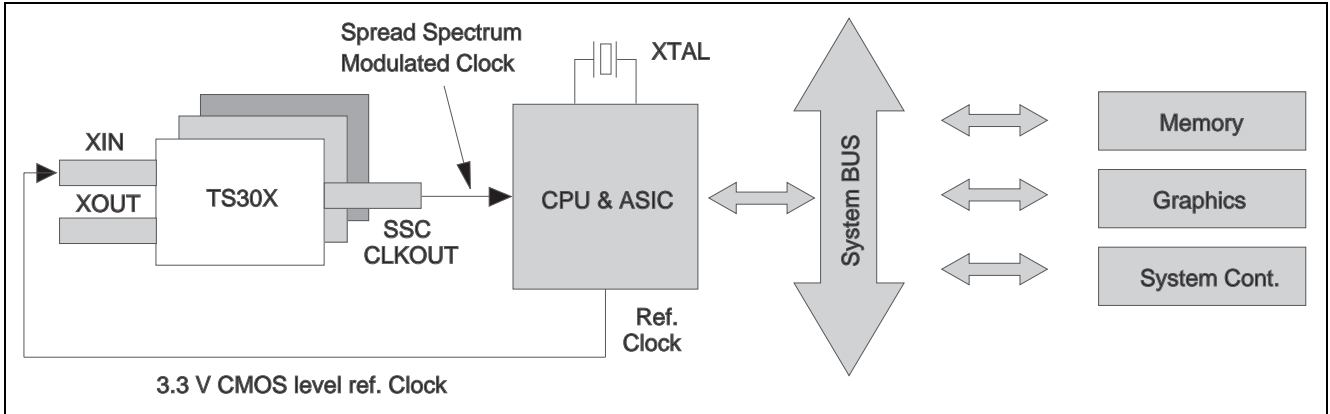


Fig 4 Ref. Clock Input Example

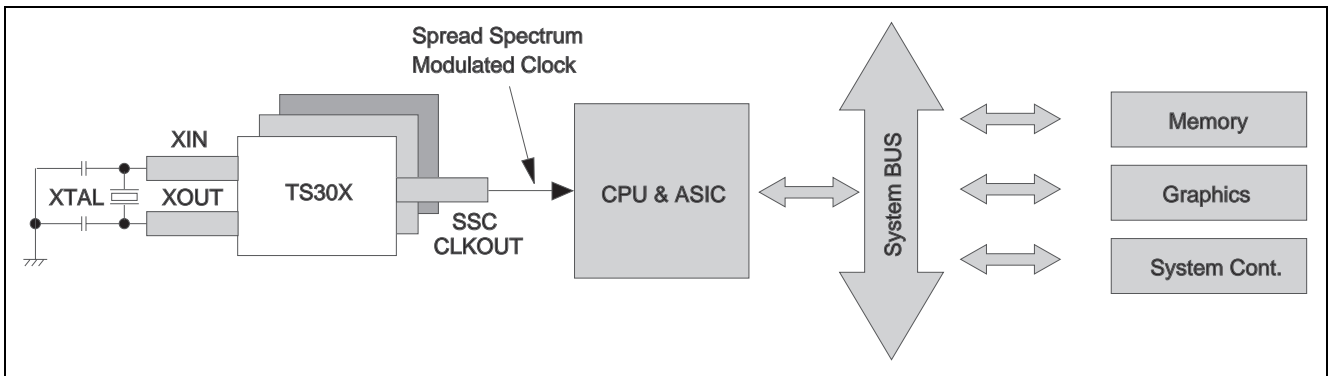
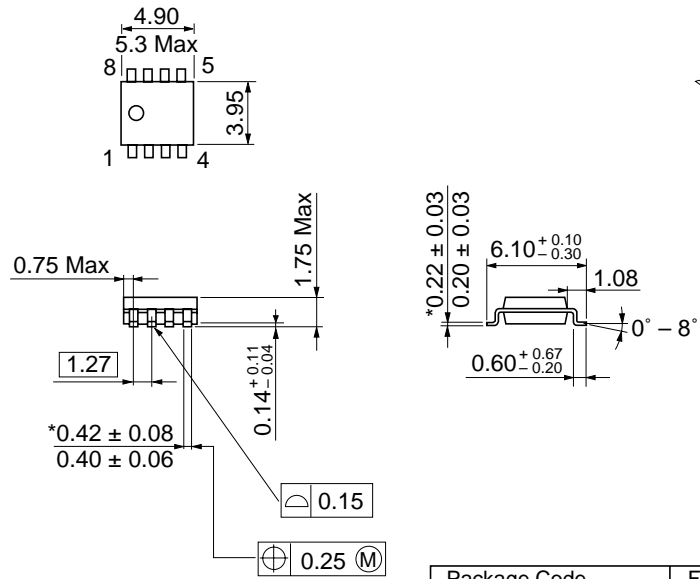


Fig 5 XTAL Ref. Clock Input Example

Package Dimensions

As of January, 2003
Unit: mm



*Dimension including the plating thickness
Base material dimension

Package Code	FP-8DC
JEDEC	Conforms
JEITA	—
Mass (reference value)	0.085 g

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